

Low trap states in *in situ* S_{N_x}/AlN/GaN metal-insulator-semiconductor structures grown by metal-organic chemical vapor deposition

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Low trap states in *in situ* SiN_x/AlN/GaN metal-insulator-semiconductor structures grown by metal-organic chemical vapor deposition

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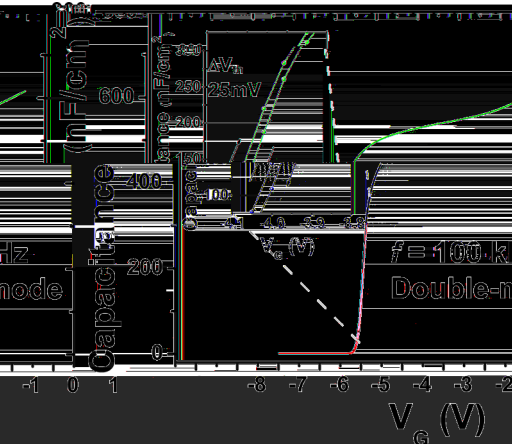
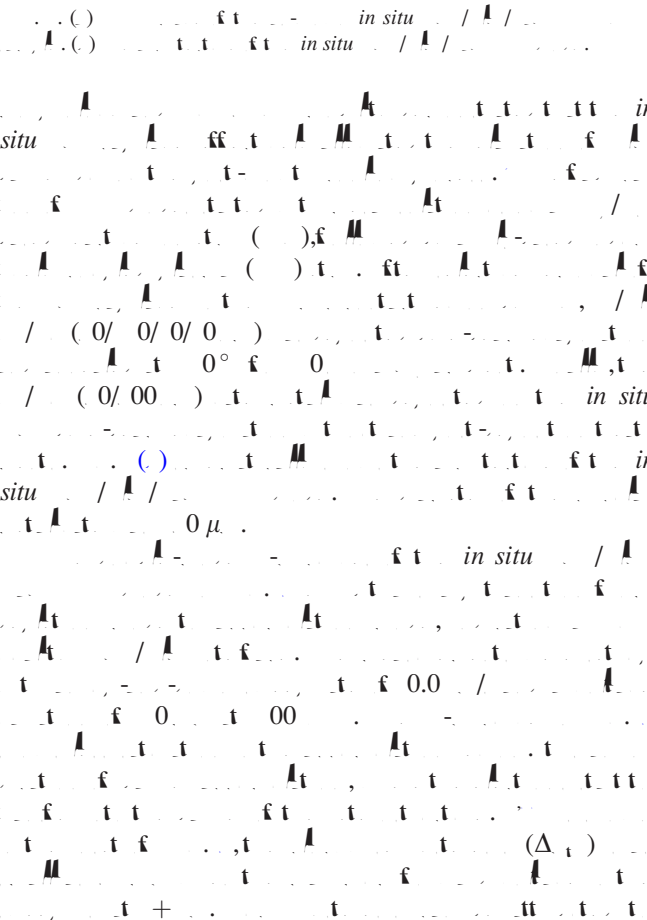
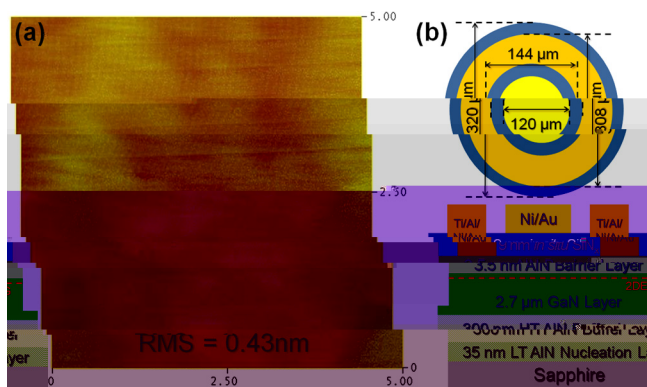
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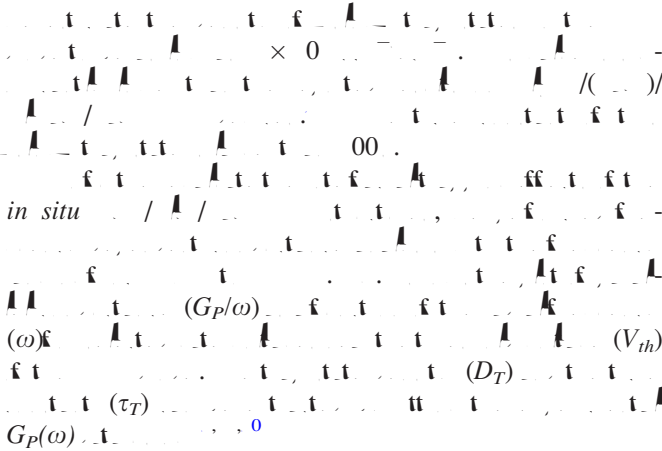
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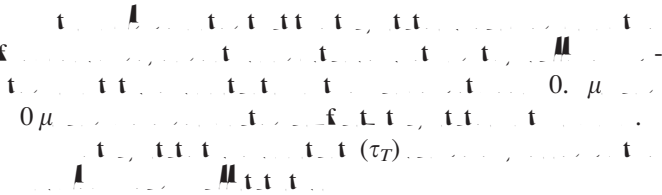
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$$D_T = C_{MIS} \cdot \Delta V_{th}/e, \quad (1)$$



$$\frac{G_p}{\omega} = \frac{qD_T}{\omega\tau_T} \left[1 + (\omega\tau_T)^2 \right]. \quad (2)$$



$$\tau_T = \frac{1}{v_{th}\sigma_n N_c} \left(\frac{E_T}{kT} \right), \quad (3)$$

